

Dual enhanced ultrafast power diode

2 February 2018

**Product data sheet** 

### 1. General description

Dual enhanced ultrafast power diode in a SOT186A (TO-220AB) plastic package.

#### 2. Features and benefits

- High thermal cycling performance
- Isolated package
- Low thermal resistance
- Soft recovery characteristic minimizes power consuming oscillations
- Very low on-state losses

#### 3. Applications

- Dual mode (DCM and CCM) PFC
- Power Factor Correction (PFC) for Interleaved Topology

### 4. Quick reference data

| Cumple of        | Devenueter                             | Conditions  |     | Turn | Mary | Links |
|------------------|--|---|-----|------|------|-------|
| Symbol           | Parameter                              | Conditions  | Min | Тур  | Max  | Unit  |
| V <sub>R</sub>   | reverse voltage                        | DC  | -   | -    | 600  | V     |
| I <sub>FRM</sub> | repetitive peak forward current        | $\delta$ = 0.5 ; $t_p$ = 25 µs; $T_h \leq ~60~^\circ\text{C};$ SQW; per diode   | -   | -    | 20   | A     |
| I <sub>FSM</sub> | non-repetitive peak<br>forward current | $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN; per diode   | -   | -    | 132  | A     |
|                  |  | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; SIN; per diode  | -   | -    | 120  | A     |
| Static chara     | acteristics                            |   |     |      | ,    |       |
| V <sub>F</sub>   | forward voltage                        | I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>  | -   | 1.4  | 2.1  | V     |
|                  |  | I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C  | -   | 1.3  | 1.9  | V     |
| Dynamic ch       | naracteristics                         | ·   |     |      |      |       |
| t <sub>rr</sub>  | reverse recovery time                  | I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/μs;<br>T <sub>i</sub> = 25 °C; <u>Fig. 5</u> | -   | 20   | 35   | ns    |

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# 5. Pinning information

| Table 2. I | Pinning in | formation               |   |                |
|------------|------------|-------------------------|---|----------------|
| Pin        | Symbol     | Description             | Simplified outline  | Graphic symbol |
| 1          | A1         | anode 1                 | mb  |                |
| 2          | К          | cathode                 |   |                |
| 3          | A2         | anode 2                 |   | K<br>sym125    |
| mb         | n.c.       | mounting base; isolated | () () ()<br>() () () ()<br>() () () ()<br>() () () ()<br>() () () () ()<br>() () () () () () () () () () () () () ( |                |

# 6. Ordering information

| Table 3. Ordering information |         |  |         |  |  |  |
|-------------------------------|---------|--|---------|--|--|--|
| Type number                   | Package | (age   |         |  |  |  |
|                               | Name    | Description  | Version |  |  |  |
| BYV410X-600                   | TO-220F | plastic single-ended package; isolated heatsink mounted; 1<br>mounting hole; 3-lead TO-220 "full pack" | SOT186A |  |  |  |

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#### 7. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol             | Parameter                       | Conditions   | Min | Max | Unit |
|--------------------|---------------------------------|--|-----|-----|------|
| V <sub>RRM</sub>   | repetitive peak reverse voltage |  | -   | 600 | V    |
| V <sub>RWM</sub>   | crest working reverse voltage   |  | -   | 600 | V    |
| V <sub>R</sub>     | reverse voltage                 | DC   | -   | 600 | V    |
| I <sub>O(AV)</sub> | average output current          | $\delta$ = 0.5 ; T <sub>h</sub> ≤ 42 °C; SQW; both diodes conducting; Fig. 1; Fig. 2 | -   | 20  | A    |
| I <sub>FRM</sub>   | repetitive peak forward current | $\delta$ = 0.5 $\ ; t_p$ = 25 µs; $T_h \leq \ 60 \ ^\circ C;$ SQW; per diode         | -   | 20  | A    |
| I <sub>FSM</sub>   | non-repetitive peak             | $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN; per diode                                | -   | 132 | А    |
|                    | forward current                 | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; SIN; per diode                                 | -   | 120 | А    |
| T <sub>stg</sub>   | storage temperature             |  | -40 | 150 | °C   |
| Tj                 | junction temperature            |  | -   | 150 | °C   |

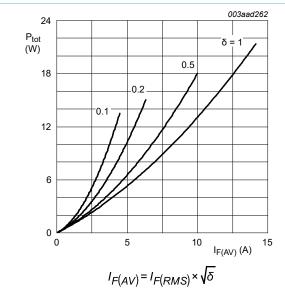


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

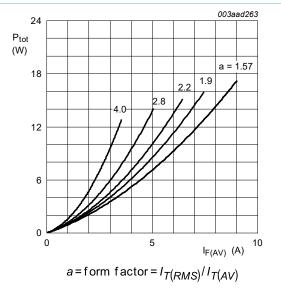


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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#### 8. Thermal characteristics

| Symbol               | Parameter  | Conditions                                     | Min | Тур | Max | Unit |
|----------------------|--|--|-----|-----|-----|------|
| R <sub>th(j-h)</sub> | thermal resistance from junction to                        | with heatsink compound; per diode;<br>Fig. 3   | -   | -   | 5   | K/W  |
|                      | heatsink   | with heatsink compound; both diodes conducting | -   | -   | 3   | K/W  |
| R <sub>th(j-a)</sub> | thermal resistance<br>from junction to<br>ambient free air |  | -   | 55  | -   | K/W  |

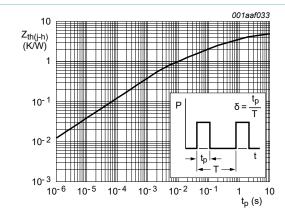


Fig. 3. Transient thermal impedance from junction to heatsink per diode as a function of pulse width

# 9. Isolation characteristics

| Table 6. Isolation     | on characteristics    |   |     |     |      |      |
|------------------------|-----------------------|---|-----|-----|------|------|
| Symbol                 | Parameter             | Conditions  | Min | Тур | Max  | Unit |
| V <sub>isol(RMS)</sub> | RMS isolation voltage | 50 Hz < f < 60 Hz; sinusoidal<br>waveform; relative humidity < 65 %;<br>clean and dust free; from all terminals<br>to external heatsink | -   | -   | 2500 | V    |
| C <sub>isol</sub>      | isolation capacitance | from cathode to external heatsink; f = 1<br>MHz   | -   | 10  | -    | pF   |

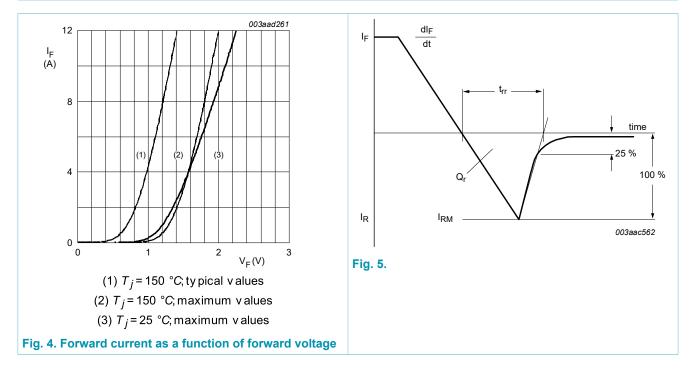
# Table 5 Thermal characteristics

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#### **10. Characteristics**

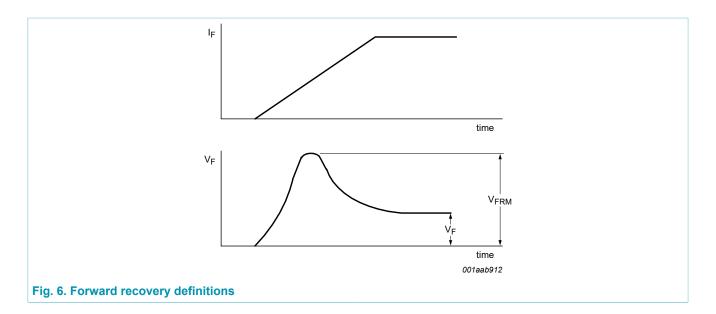
| Symbol          | Parameter                        | Conditions  | Min | Тур | Max | Unit |
|-----------------|----------------------------------|---|-----|-----|-----|------|
| Static chara    | acteristics                      | · · · ·   |     |     |     |      |
| V <sub>F</sub>  | forward voltage                  | I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>  | -   | 1.4 | 2.1 | V    |
|                 |                                  | I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C  | -   | 1.3 | 1.9 | V    |
| I <sub>R</sub>  | reverse current                  | V <sub>R</sub> = 600 V; T <sub>j</sub> = 100 °C   | -   | 1   | 1.5 | mA   |
|                 |                                  | V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C  | -   | 13  | 50  | μA   |
| Dynamic ch      | naracteristics                   | · · · ·   |     |     |     |      |
| t <sub>rr</sub> | reverse recovery time            | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s};$<br>$T_j = 25 \text{ °C}; \text{ Fig. 5}$ | -   | 20  | 35  | ns   |
| I <sub>RM</sub> | peak reverse recovery<br>current | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s};$<br>Fig. 5                                | -   | 1.4 | 1.9 | A    |
| Q <sub>r</sub>  | recovered charge                 | I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/μs   | -   | 15  | 28  | nC   |
| V <sub>FR</sub> | forward recovery voltage         | I <sub>F</sub> = 1 A; dI <sub>F</sub> /dt = 100 A/μs; <u>Fig. 6</u>   | -   | 3.2 | -   | V    |



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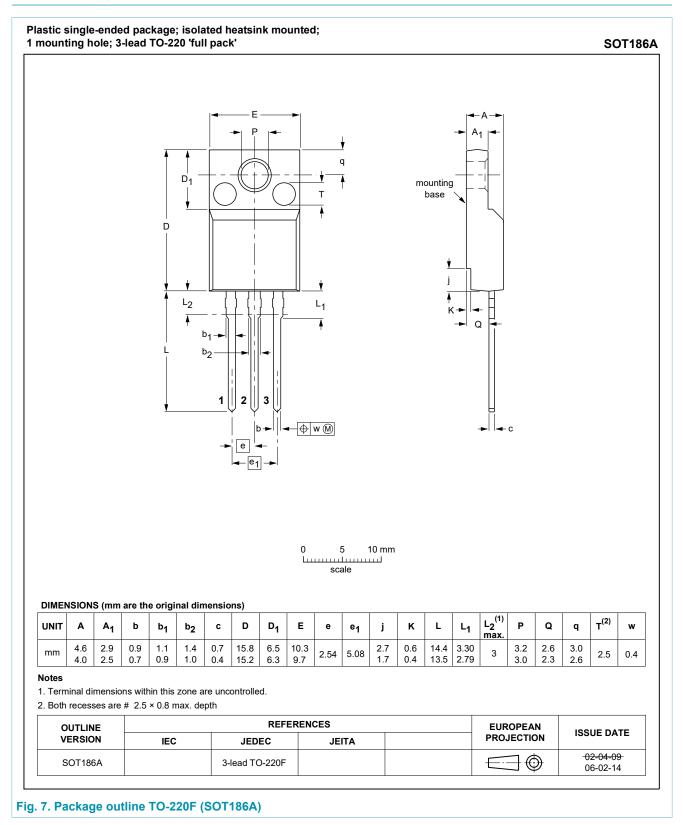
# BYV410X-600

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#### 11. Package outline



#### Dual enhanced ultrafast power diode

#### 12. Legal information

#### **Data sheet status**

| Document<br>status [1][2]            | Product<br>status [ <u>3]</u> | Definition  |
|--------------------------------------|-------------------------------|---|
| Objective<br>[short] data<br>sheet   | Development                   | This document contains data from<br>the objective specification for product<br>development. |
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